

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/634174
	Filing Date	August 5, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2826 2823
	Examiner Name	Tran, Tan J. Garcia
Sheet 1 of 7	Attorney Docket No: 1303.102US1	

US PATENT DOCUMENTS						
Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
JAG	US20020001965	01/03/2002	Forbes, Leonard	438	734	07/22/1997
JAG	US20020070421	06/13/2002	Ashburn, Stanton P.	257	510	02/08/2002
JAG	US20020175330	11/28/2002	Geusic, Joseph			
JAG	US20020185686	12/12/2002	Christiansen, Silke H., et al.	257	347	04/03/2002
JAG	US2003/0227072	12/11/2003	Forbes, Leonard	257	616	06/10/2002
JAG	US20030027406	02/06/2003	Malone, Farris D.	438	471	08/01/2001
JAG	US20030133683	07/17/2003	Forbes, Leonard, et al.			
JAG	US20030190796	10/09/2003	Geusic, Joseph			
JAG	US20030201468	10/30/2003	Christiansen, H., et al.	257	200	04/30/2003
JAG	US20030218189	11/27/2003	Christiansen, Silke H., et al.	257	200	11/19/2002
JAG	US-4,241,359	12/23/1980	Izumi, Katsutoshi, et al.	257	386	03/02/1978
JAG	US-4,314,595	02/09/1982	Yamamoto, , et al.	148	1.5	01/08/1980
JAG	US-4,589,928	05/20/1986	Dalton, John V.	438	142	08/21/1984
JAG	US-4,717,681	01/05/1988	Curran, Patrick A.	438	314	05/19/1986
JAG	US-5,426,061	06/20/1995	Sopori, Bhushan L.	438	475	09/06/1994
JAG	US-5,443,661	08/22/1995	Oguro, Shizuo, et al.	148	33.5	07/27/1994
JAG	US-5,461,243	10/24/1995	Ek, Bruce A., et al.	257	190	10/29/1993
JAG	US-5,646,053	07/08/1997	Schepis, Dominic J.	438	402	12/20/1995
JAG	US-5,661,044	08/26/1997	Holland, Orin W., et al.	438	766	06/15/1995
JAG	US-5,691,230	11/25/1997	Forbes, Leonard	437	62	09/04/1996
JAG	US-5,759,898	06/02/1998	Ek, Bruce, et al.	438	291	12/19/1996
JAG	US-5,840,590	11/24/1998	Myers Jr., Samuel M., et al.	438	471	12/01/1993
JAG	US-5,879,996	03/09/1999	Forbes, Leonard	438	289	09/18/1996
JAG	US-5,963,817	10/05/1999	Chu, Jack O., et al.	438	410	10/16/1997
JAG	US-6,001,711	12/14/1999	Hashimoto, Takasuke	438	473	03/09/1998
JAG	US-6,022,793	02/08/2000	Wijaranakula, Witawat, et al.	438	473	10/21/1997
JAG	US-6,093,623	07/25/2000	Forbes, Leonard	438	455	08/04/1998
JAG	US-6,093,624	07/25/2000	Letavic, Theodore J., et al.	438	462	12/23/1997
JAG	US-6,174,784	01/16/2001	Forbes, Leonard	438	405	11/14/1997
JAG	US-6,204,145	03/20/2001	Noble, Wendell P.	438	412	08/07/1998
JAG	US-6,228,694	05/08/2001	Doyle, Brian S., et al.	438	199	06/28/1999
JAG	US-6,251,751	06/26/2001	Chu, Jack O., et al.	438	439	04/13/1999
JAG	US-6,274,460	08/14/2001	Delgado, Jose A., et al.	438	476	06/17/1999
JAG	US-6,309,950	10/30/2001	Forbes, Leonard	438	455	03/23/2000
JAG	US-6,315,826	11/13/2001	Muramatsu, Satoru	117	95	06/22/2000

EXAMINER

Joanne A. Garcia

DATE CONSIDERED

July 22, 2004

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	<i>Complete if Known</i>	
	Application Number	10/634174
	Filing Date	August 5, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2826 2823
	Examiner Name	Tran, Ten J. Garcia
Sheet 2 of 7	Attorney Docket No: 1303.102US1	

JAG	US-6,338,805	01/15/2002	Anderson, Gary L.	216	89	07/14/1999
JAG	US-6,339,011	01/15/2002	Gonzalez, Fernando , et al.	438	473	03/05/2001
JAG	US-6,376,336	04/23/2002	Buynoski, Matthew S.	438	476	02/01/2001
JAG	US-6,377,070	04/23/2002	Forbes, Leonard	326	41	02/09/2001
JAG	US-6,424,001	07/23/2002	Forbes, Leonard , et al.	257	315	02/09/2001
JAG	US-6,448,601	09/10/2002	Forbes, Leonard , et al.	257	302	02/09/2001
JAG	US-6,478,883	11/12/2002	Tamatsuka, Masaro , et al.	148	33.2	04/18/2000
JAG	US-6,496,034	12/17/2002	Forbes, Leonard , et al.	326	041	02/09/2001
JAG	US-6,531,727	03/11/2003	Forbes, Leonard , et al.	257	302	02/09/2001
JAG	US-6,538,330	03/25/2003	Forbes, Leonard	257	777	03/23/2000
JAG	US-6,559,491	05/06/2003	Forbes, Leonard , et al.	257	296	02/09/2001
JAG	US-6,566,682	05/20/2003	Forbes, Leonard	257	51	02/09/2001
JAG	US-6,582,512	06/24/2003	Geusic, Joseph E., et al.	117	3	05/22/2001
JAG	US-6,593,625	07/15/2003	Christiansen, Silke H., et al.	257	347	04/03/2002
JAG	US-6,597,203	07/22/2003	Forbes, Leonard	326	98	03/14/2001
JAG	US-6,649,476	11/18/2003	Forbes, Leonard	438	268	02/15/2001

FOREIGN PATENT DOCUMENTS						
Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²
JAG	EP-434984	09/03/1991	Lindberg, Keith J., et al.	H01L	21/322	
JAG	WO-WO02097982	12/05/2002	Pavio, Anthony M., et al.	H03 G	3/10	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
JAG		"Cornell Demonstrates a Universal Substrate", <u>Compound Semiconductor</u> , 3(2), (March/April 1997), 27-29	
JAG		ABE, T , "Silicon Wafer-Bonding Process Technology for SOI Structures", <u>Extended Abstracts of the 22nd (1990 International) Conference on Solid State Devices and Materials</u> , (1990), 853-856	
JAG		AUBERTON-HERVE, A J., "SOI: Materials to Systems", <u>International Electron Devices Meeting. Technical Digest</u> , (1996), 3-10	
JAG		AUTUMN, KELLAR , et al., "Adhesive force of a single gecko foot-hair", <u>Nature</u> , 405(6787), (June 2000), 681-685	
JAG		AUTUMN, KELLAR , et al., "Evidence for van der Waals adhesion in gecko setae.", <u>Proceedings of the National Academy of Science U S A.</u> , 99(19), (September 17, 2002), 12252-6	

EXAMINER

DATE CONSIDERED

Substitute Disclosure Statement Form (PTO-1449)
* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/634174
	Filing Date	August 5, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2826 2823
	Examiner Name	Tran, Tan J. Garcia
Sheet 3 of 7	Attorney Docket No: 1303.102US1	

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
JAG		BAGINSKI, T. A., "Back-side germanium ion implantation gettering of silicon", <u>Journal of the Electrochemical Society</u> , 135(7), Dept of Electrical Engineering, Auburn Univ, AL, (July 1988), 1842-3	
JAG		BELFORD, RONA E., "Performance-Augmented CMOS Using Back-End Uniaxial Strain", <u>IEEE Device Research Conference</u> , (2002), 41-42	
JAG		BERTI, M., "Composition and Structure of Si-Ge Layers Produced by Ion Implantation and Laser Melting", <u>Journal of Materials Research</u> , 6(10), (October 1991), 2120-2126	
JAG		BERTI, M., "Laser Induced Epitaxial Regrowth of Si _{1-x} Ge _x /Si Layers Produced by Ge Ion Implantation", <u>Applied Surface Science</u> , 43, (1989), 158-164	
JAG		BIALAS, F., et al., "Intrinsic Gettering of 300 mm CZ Wafers", <u>Microelectronic Engineering</u> , 56(1-2), (May 2001), 157-63	
JAG		BIEVER, CELESTE, "Secret of 'strained silicon' revealed: behind closed doors, Intel has perfected a novel way to improve chip performance.", <u>New Scientist</u> , 180(i2426-2428), (December 20, 2003), 27	
JAG		BINNS, M. J., et al., "The Realization of Uniform and Reliable Intrinsic Gettering in 200mm P- & P/P Wafers for a Low Thermal Budget 0.18 μ m Advanced CMOS Logic Process", <u>Diffusion and Defect Data Pt.B: Solid State Phenomena</u> , 82-84, (2001), 387-92	
JAG		BREQUEL, H., "Structural characterization and crystallization behaviour of silicon oxycarbide glasses", <u>XIX International Congress on Glass, Proceedings of the Congress held at the Edinburgh International Conference Centre, Scotland, July 1-6, 2001. Contains invited papers volume and extended abstracts of all the papers and posters presented during the Congress.</u> , (2001),	
JAG		BRONNER, G. B., et al., "Physical Modeling of Backside Gettering", <u>Impurity Diffusion and Gettering in Silicon Symposium</u> , Sponsor: Mater. Res. Soc, Nov 1984, Boston, MA, (1985), 27-30	
JAG		BROWN, CHAPPELL, "Bonding twist hints at universal substrate", <u>EETimes</u> , (1997), 2 pages	
JAG		BRUEL, M., et al., "Smart-Cut: a new silicon on insulator material technology based on hydrogen implantation and wafer bonding", <u>Japanese Journal of Applied Physics, Part 1 (Regular Papers, Short Notes & Review Papers)</u> , 36(3B), (1997), 1636-1641	
JAG		CHEN, XIANGDONG, et al., "Vertical P-MOSFETs with heterojunction between source/drain and channel", <u>IEEE Device Research Conference</u> , (2000), 25-26	
JAG		CHILTON, B T., et al., "Solid phase epitaxial regrowth of strained Si(1-x)Ge(x)/Si strained layer structures amorphized by ion implantation", <u>Applied Physics Letters</u> , 54(1), (January 2, 1989), 42-44	
JAG		CHOE, K. S., et al., "Minority-Carrier Lifetime Optimization in Silicon MOS Devices by Intrinsic Gettering", <u>Journal of Crystal Growth</u> , 218(2-4), (September 2000), 239-44	

EXAMINER

Joanna A. Garcia

DATE CONSIDERED

July 22, 2004

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/634174
	Filing Date	August 5, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2826 2823
	Examiner Name	Tran, Tan J. Garcia
Sheet 4 of 7		Attorney Docket No: 1303.102US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
JAG		CLARK, DON , et al., "Intel unveils tiny new transistors: Process handles circuits 1/2000th the width of a human hair", <u>The Wall Street Journal</u> , (August 13, 2002),3 pages	
JAG		CLIFTON, P A., et al., "A process for strained silicon n-channel HMOSFETs", <u>ESSDERC'96. Proceedings of the 26th European Solid State Device Research Conference</u> , (September 1996),519-22	
JAG		DUBBELDAY, W B., et al., "Oscillatory strain relaxation in solid phase epitaxially regrown silicon on sapphire", <u>Proceedings of the First International Workshop Lattice Mismatched Thin Films</u> , (September 13-15, 1998),13-17	
JAG		FISCHEITTI, M V., et al., "Band structure, deformation potentials, and carrier mobility in strained Si, Ge, and SiGe alloys", <u>Journal of Applied Physics</u> , 80(4), (August 15, 1996),2234-2252	
JAG		FOURNEL, F , et al., "Ultra High Precision Of The Tilt/Twist Misorientation Angles In Silicon/Silicon Direct Wafer Bonding", <u>Abstract - Electronic Materials Conference</u> , (June 2002),9	
JAG		GARCIA, G A., et al., "High-quality CMOS in thin (100 nm) silicon on sapphire", <u>IEEE Electron Device Letters</u> , 9(1), (January 1988),32-34	
JAG		GODBOLE, H. , et al., "An Investigation of Bulk Stacking Faults in Silicon Using Photocapacitance Transient Spectroscopy", <u>Materials Letters</u> , 8(6-7), Dept of Electr & Comput Engr, Oregon State Univ, Corvallis OR,(July 1989),201-3	
JAG		GONG, S. S., et al., "Implantation Gettering in Silicon", <u>Solid-State Electronics</u> , 30(2), (February 1987),209-11	
JAG		GRAF, D. , et al., "300 mm epi pp- wafer: is there sufficient gettering?", <u>High Purity Silicon VI. Proceedings of the Sixth International Symposium (Electrochemical Society Proceedings Vol. 2000-17) (SPIE Vol.4218)</u> , (2000),319-30	
JAG		HADDAD, H. , et al., "Carbon Doping Effects on Hot Electron Trapping", <u>28th Annual Proceedings. Reliability Physics 1990</u> , (March 1990),288-9	
JAG		HADDAD, H. , et al., "Electrical Activity of Bulk Stacking Faults in Silicon", <u>Materials Letters</u> , 7(3), Hewlett-Packard Northwest Integrated Circuits Div, Corvallis OR,(September 1988),99-101	
JAG		HARENDT, CHRISTINE , "Silicon on Insulator Material by Wafer Bonding", <u>Journal of Electronic Materials</u> , 20(3), (March 1991),267-77	
JAG		IYER, S S., "Separation by Plasma Implantation of Oxygen (SPIMOX) operational phase space", <u>IEEE trans. on Plasma Science</u> , 25, (1997),1128-1135	
JAG		KALAVADE, PRANAV , et al., "A novel sub-10 nm transistor", <u>58th DRC. Device Research Conference. Conference Digest</u> , (June 19-21, 2000),71-72	
JAG		KANG, J. S., et al., "Gettering in Silicon", <u>Journal of Applied Physics</u> , 65(8), Center for Solid State Electron Res., Arizona State Univ., Tempe, AZ,(April 15, 1989),2974-85	

EXAMINER

Juanita A. Garcia

DATE CONSIDERED

July 22, 2004

Substitute Disclosure Statement Form (PTO-1449)
* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/634174
	Filing Date	August 5, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2826 2823
	Examiner Name	Tran, Tan J. Garcia
Sheet 5 of 7	Attorney Docket No: 1303.102US1	

JAG	KOSTRZEWA, M , et al., "Testing the Feasibility of strain relaxed InAsP and InGaAs compliant substrates", <u>EMC 2003 International Conference Indium Phosphide and Related Materials. Conference Proceedings</u> , Other authors: G. Grenet et al,(6/2003),8-9	
JAG	KUNG, C. Y., et al., "The effect of carbon on oxygen precipitation in high carbon CZ silicon crystals", <u>Materials Research Bulletin</u> , 18(12), Silicon Materials Div., Fairchild Camera & Instrument Corp, Healdsburg, CA,(December 1983),1437-41	
JAG	LASKY, J. B., "Wafer Bonding for Silicon-on-Insulator Technologies", <u>Applied Physics Letters</u> , 48(1), (January 6, 1986),78-80	
JAG	LI, Y. X., et al., "New intrinsic gettering process in Czochralski-silicon wafer", <u>6th International Conference on Solid-State and Integrated Circuit Technology. Proceedings</u> , 1(1), (2001),277-9	
JAG	LOO, Y L., et al., "Contact Printing With Nanometer Resolution", <u>Device Research Conference</u> , (June 2002),149-150	
JAG	LU, D, , "Bonding Silicon Wafers by Use of Electrostatic Fields Followed by Rapid Thermal Heating", <u>Materials Letters</u> , 4(11), (October 1986),461-464	
JAG	MIZUNO, T , et al., "Advanced SOI-MOSFETs with Strained-Si Channel for High Speed CMOS Electron/Hole Mobility Enhancement", <u>2000 Symposium on VLSI Technology. Digest of Technical Papers</u> , (2000),210-211	
JAG	MORAN, PETER , "Strain Relaxation in Wafer-Bonded SiGe/Si Heterostructures Due to Viscous Flow of an Underlying Borosilicate Glass", <u>Electronic Materials Conference</u> , Santa Barbara, June 2002, Abstract,(June 2002),Pgs. 8-9	
JAG	MUMOLA, P. B., et al., "Recent advances in thinning of bonded SOI wafers by plasma assisted chemical etching", <u>Proceedings of the Third International Symposium on Semiconductor Wafer Bonding: Physics and Applications</u> , (1995),28-32	
JAG	NAYAK, D.K. , "High performance GeSi quantum-well PMOS on SIMOX", <u>International Electron Devices Meeting 1992. Technical Digest</u> , (1992),777-80	
JAG	NICHOLS, F A., "Surface-(interface) and volume-diffusion contributions to morphological changes driven by capillarity", <u>Transactions of the American Institute of Mining, Metallurgical and Petroleum Engineers</u> , 233(10), (1965),1840-8	
JAG	O'NEILL, A G., et al., "High speed deep sub-micron MOSFET using high mobility strained silicon channel", <u>ESSDERC '95. Proceedings of the 25th European Solid State Device Research Conference</u> , (September 1995),109-12	
JAG	OMI, HIROO , et al., "Semiconductor Surface with Strain Control", http://www.brl.ntt.co.jp/J/kouhou/katsudou/report00/E/report04_e.html ,	
JAG	OR, B S., et al., "Annealing effects of carbon in n-channel LDD MOSFETs", <u>IEEE Electron Device Letters</u> , 12(11), Dept of Electrical & Computing Engr, Oregon State Univ, Corvallis OR,(November 1991),596-8	
JAG	OUYANG, Q , et al., "Bandgap Engineering in Deep Submicron Vertical pMOSFETs", <u>IEEE 58th DRC. Device Research Conference. Conference Digest</u> , (2000),27-28	
JAG	PAINE, D. C., "The Growth of Strained Si _{1-x} Ge _x Alloys on (100) Silicon Using Solid Phase Epitaxy", <u>Journal of Materials Research</u> , 5(5), (May 1990),1023-1031	

EXAMINER

Joanne J. Garcia

DATE CONSIDERED

July 29, 2004

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: (Initial if reference considered, whether or not citation is in conformance with MPEP 809. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.) Applicant's unique citation designation number (optional) * Applicant is to place a check mark here if English language Translation is attached

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/634174
	Filing Date	August 5, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2826 2823
	Examiner Name	Fran, Tan J. Garcia
Sheet 6 of 7	Attorney Docket No: 1303.102US1	

JAG	PEOPLE, R. , "Calculation of critical layer thickness versus lattice mismatch for GexSi1-x/Si strained-layer heterostructures", <u>Applied Physics Letters</u> , 47(3), (August 1, 1985),322-4	
JAG	RIM, KERN , et al., "Fabrication and analysis of deep submicron strained-Si n-MOSFET's", <u>IEEE Transactions on Electron Devices</u> , 47(7), (July 2000),1406-1415	
JAG	RIM, KERN , et al., "Strained Si NMOSFETs for High Performance CMOS Technology", <u>2001 Symposium on VLSI Technology. Digest of Technical Papers</u> , (2001),59-60	
JAG	RIM, KERN , et al., "Transconductance enhancement in deep submicron strained Si n-MOSFETs", <u>International Electron Devices Meeting 1998. Technical Digest</u> , (1998),707-710	
JAG	RUBIN, L , et al., "Effective gettering of oxygen by high dose, high energy boron buried layers", <u>1998 International Conference on Ion Implantation Technology. Proceedings</u> , 2(2), (1998),1010-13	
JAG	SATO, TSUTOMU , "A New Substrate Engineering for the Formation of Empty Space in Silicon (ESS) Induced by Silicon Surface Migration", <u>IEDM Digest, paper 20.6.1</u> , (1999),20.6.1-20.6.4	
JAG	SATO, T , "Trench transformation technology using hydrogen annealing for realizing highly reliable device structure with thin dielectric films", <u>1998 Symposium on VLSI Technology Digest of Technical Papers</u> , (1998),206-7	
JAG	SUGIYAMA, N , et al., "Formation of strained-silicon layer on thin relaxed-SiGe/SiO/sub 2//Si structure using SIMOX technology", <u>Thin Solid Films</u> , 369(1-2), (July 2000),199-202	
JAG	TAKAGI, SHIN-ICHI , "Strained-Si- and SiGe-On-Insulator (Strained-SOI and SGOI) MOSFETs for High Performance/Low Power CMOS Application", <u>IEEE Device Research Conference, 2002. 60th DRC. Conference Digest</u> , (2002),37-40	
JAG	TAN, T. Y., et al., "Intrinsic gettering by oxide precipitate induced dislocations in Czochralski Si", <u>Applied Physics Letters</u> , 30(4), IBM System Products Div., Essex Junction, VT,(February 15, 1977),175-6	
JAG	VERDONCKT-VANDEBROEK,, SOPHIE , et al., "SiGe-Channel Heterojunction p-MOSFET's", <u>IEEE Transactions on Electron Devices</u> , 41(1), (January 1994),90-101	
JAG	WELSER, J , et al., "Strain dependence of the performance enhancement in strained-Si n-MOSFETs", <u>IEEE International Electron Devices Meeting 1994. Technical Digest</u> , (December 11-14, 1994),373-376	
JAG	WHITWER, F. D., et al., "DLTS characterization of precipitation induced microdefects", <u>Materials Issues in Silicon Integrated Circuit Processing Symposium</u> , (April 1986),53-57	
JAG	WIJARANAKULA, W. , et al., "Effect of Pre- and Postepitaxial Deposition Annealing on Oxygen Precipitation in Silicon", <u>Journal of Materials Research</u> , 1(5), Dept of Electr & Comput Eng, Oregon State Univ, Corvallis, OR,(September-October 1986),698-704	

EXAMINER

Joanna A. Garcia

DATE CONSIDERED

July 23, 2004

Substitute Disclosure Statement Form (PTO-1449)

* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control number.

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)	Complete if Known	
	Application Number	10/634174
	Filing Date	August 5, 2003
	First Named Inventor	Forbes, Leonard
	Group Art Unit	2826 2823
	Examiner Name	Tran, Tan J. Garcia
Sheet 7 of 7	Attorney Docket No: 1303.102US1	

JAG	WIJARANAKULA, W. , et al., "Effect of preanneal heat treatment on oxygen precipitation in epitaxial silicon", <u>Materials Issues in Silicon Integrated Circuit Processing Symposium</u> , (April 1986),139-44	
JAG	WIJARANAKULA, W. , et al., "Internal Gettering Heat Treatments and Oxygen Precipitation in Epitaxial Silicon Wafers", <u>Journal of Materials Research</u> , 1(5), Dept of Electr & Comput. Eng, Oregon State Univ., Corvallis, OR,(September-October 1986),693-7	
JAG	WIJARANAKULA, W. , et al., "Oxygen precipitation in p/p+(100) epitaxial silicon material", <u>Journal of the Electrochemical Society</u> , 134(9), SEH America, Inc., Mater. Characterization Lab., Vancouver, WA,(September 1987),2310-16	
JAG	WILD, DIPL.ING. M., "Laser Assisted Bonding of Silicon and Glass in Micro-System Technology", <u>http://www.ilt.fhg.de/eng/jb00-s42.html</u> , Fraunhofer ILT - jb00-s42,(2003),1	
JAG	XUAN, PEIQI , et al., "60nm Planarized Ultra-thin Body Solid Phase Epitaxy MOSFETs", <u>IEEE Device Research Conference, Conference Digest. 58th DRC</u> , (June 19-21, 2000),67-68	
JAG	YANG, D. , et al., "Intrinsic Gettering in Nitrogen Doped Czochralski Crystal Silicon", <u>High Purity Silicon VI. Proceedings of the Sixth International Symposium (Electrochemical Society Proceedings Vol. 2000-17) (SPIE Vol.4218)</u> , (2000),357-61	
JAG	YANG, DEREN , et al., "Nitrogen in Czochralski Silicon", <u>2001 6th International Conference on Solid-State and Integrated Circuit Technology. Proceedings</u> , 1(1), (2001),255-60	
JAG	YIN, HAIZHOU , "High Ge-Content Relaxed Si1-xGex Layers by Relaxation on Complaint Substrate with Controlled Oxidation", <u>Electronic Materials Conference</u> , Santa Barbara, June 2002, (June 2002),8	
JAG	ZHU, Z H., et al., "Wafer bonding and its application on compliant universal (CU) substrates", <u>Conference Proceedings, 10th Annual Meeting IEEE Lasers and Electro-Optics Society</u> , (November 10-13, 1996),31	
JAG	ZHU, Z H., et al., "Wafer bonding technology and its applications in optoelectronic devices and materials", <u>IEEE Journal of Selected Topics in Quantum Electronics</u> , (June 1997),927 - 936	

EXAMINER

J. Garcia

DATE CONSIDERED

July 22 2004

Substitute Disclosure Statement Form (PTO-1449)

EXAMINER: Initial if reference considered, whether or not claim is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 1 Applicant's unique citation designation number (optional) 2 Applicant is to place a check mark here if English language Translation is attached